

# 2SD2573

## Silicon NPN triple diffusion planar type

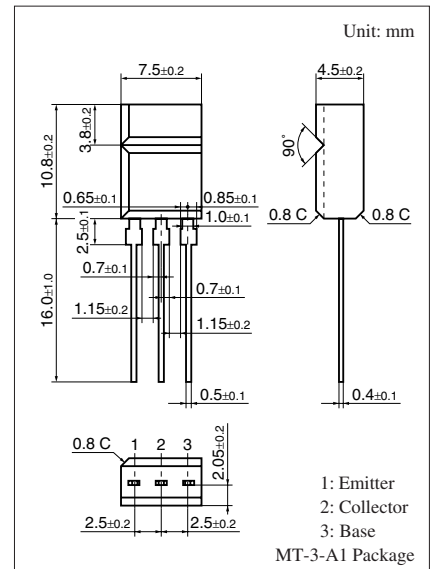
For high current amplification, power amplification

### ■ Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Allowing supply with the radial tapping

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	80	V
Collector-emitter voltage (Base open)	$V_{CEO}$	60	V
Emitter-base voltage (Collector open)	$V_{EBO}$	6	V
Collector current	$I_C$	3	A
Peak collector current	$I_{CP}$	6	A
Collector power dissipation	$T_C = 25^\circ\text{C}$ $P_C$	1.5	W
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$



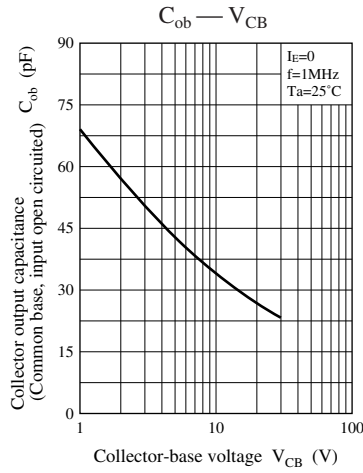
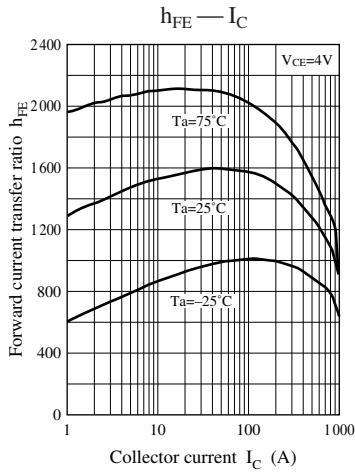
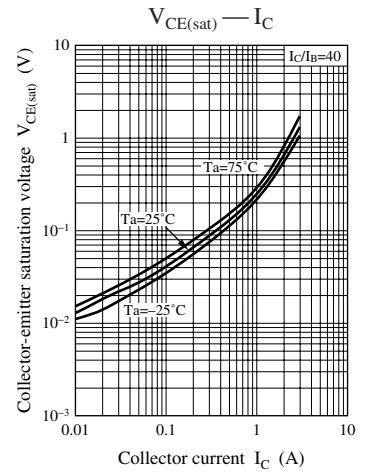
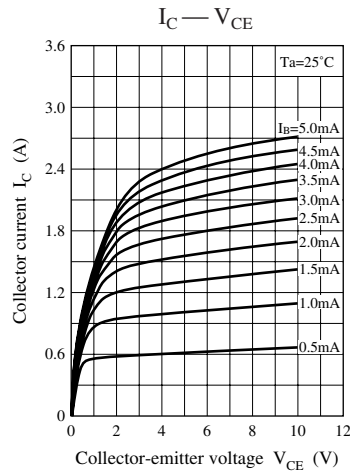
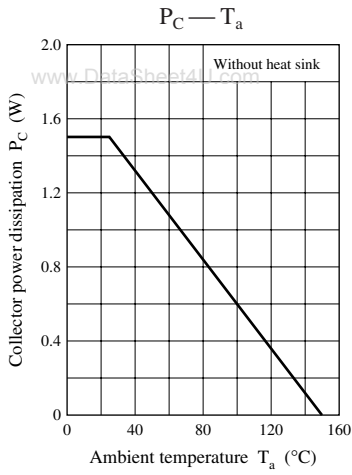
### ■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 25\text{ mA}$ , $I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 80\text{ V}$ , $I_E = 0$			100	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 40\text{ V}$ , $I_B = 0$			100	$\mu\text{A}$
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6\text{ V}$ , $I_C = 0$			100	$\mu\text{A}$
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 4\text{ V}$ , $I_C = 0.5\text{ A}$	500		2500	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 2\text{ A}$ , $I_B = 0.05\text{ A}$			1.0	V
Transition frequency	$f_T$	$V_{CE} = 12\text{ V}$ , $I_C = 0.2\text{ A}$ , $f = 10\text{ MHz}$		50		MHz

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	P	Q	R
$h_{FE}$	500 to 1000	800 to 1500	1200 to 2500



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